

ABSTRACT

A method of testing an integrated circuit is provided, which includes providing a semiconductor substrate having a semiconductor device provided thereon. A first dielectric layer is formed over the semiconductor substrate and a first channel is formed in the first dielectric layer in contact with the semiconductor device. A first contact pad mask layer is
5 formed and a first contact pad in the first contact pad mask layer is formed in contact with the first channel. The first contact pad is used to test the first channel and the semiconductor device and the first contact pad mask layer and the first contact pad are removed.